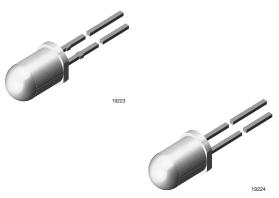


Vishay Semiconductors

High Intensity LED, ∅ 5 mm Clear Package



DESCRIPTION

This LED contains the double heterojunction (DH) GaAlAs on GaAs technology.

This deep red LED can be utilized over a wide range of drive current. It can be DC or pulse driven to achieve desired light output.

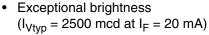
A clear 5 mm package is used to provide an extremely high light intensity of more than 2000 mcd at a very narrow viewing angle.

PRODUCT GROUP AND PACKAGE DATA

· Product group: LED Package: 5 mm

· Product series: standard Angle of half intensity: ± 4°

FEATURES





- Narrow viewing angle ($\varphi = \pm 4^{\circ}$)
- · Low forward voltage
- 5 mm (T-13/4") clear package
- · Very high intensity even at low drive currents
- · Deep red color
- · Categorized for luminous intensity
- Outstanding material efficiency
- Lead (Pb)-free device
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- Bright ambient lighting conditions
- · Battery powered equipment
- · Indoor and outdoor information displays
- Portable equipment
- · Telecommunication indicators
- General use

PARTS TABLE				
PART	COLOR, LUMINOUS INTENSITY	TECHNOLOGY		
TLDR5800/6800	Red, $I_V \ge 1000 \text{ mcd}$	GaAIAs on GaAs		

ABSOLUTE MAXIMUM RATINGS ¹⁾ TLDR5800/6800				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage ²⁾		V _R	6	V
DC Forward current		I _F	50	mA
Surge forward current	t _p ≤ 10 μs	I _{FSM}	1	A
Power dissipation		P _V	100	mW
Junction temperature		T _j	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C

TLDR5800/TLDR6800

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ABSOLUTE MAXIMUM RATINGS ¹⁾ TLDR5800/6800				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Storage temperature range		T _{stg}	- 55 to + 100	°C
Soldering temperature	$t \le 5 \text{ s, 2 mm from body}$	T _{sd}	260	°C
Thermal resistance junction/ ambient		R _{thJA}	350	K/W

Note:

²⁾ Driving the LED in reverse direction is suitable for a short term application

OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ TLDR5800/6800, RED						
PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP.	MAX	UNIT
Luminous intensity	I _F = 20 mA	I _V	1000	2500		mcd
Dominant wavelength	I _F = 20 mA	λ_{d}		648		nm
Peak wavelength	I _F = 20 mA	λ_{p}		650		nm
Angle of half intensity	I _F = 20 mA	φ		± 4		deg
Forward voltage	I _F = 20 mA	V _F		1.8	2.2	V
Reverse current	V _R = 6 V	I _R			10	μΑ
Junction capacitance	V _R = 0, f = 1 MHz	C _j		50		pF

Note:

 $^{^{1)}}$ T_{amb} = 25 °C, unless otherwise specified

LUMINOUS INTENSITY CLASSIFICATION				
GROUP	LUMINOUS IN	TENSITY (MCD)		
STANDARD	MIN	MAX		
EE	1000	2000		
FF	1350	2700		
GG	1800	3600		
НН	2400	4800		
II	3200	6400		
KK	4300	8600		
LL	5750	11500		
MM	7500	15000		
NN	10000	20000		

Note:

Luminous intensity is tested at a current pulse duration of 25 ms and an accuracy of \pm 11 %.

The above type numbers represent the order groups which include only a few brightness groups. Only one group will be shipped on each bag (there will be no mixing of two groups in each bag).

In order to ensure availability, single brightness groups will not be orderable.

In a similar manner for colors where wavelength groups are measured and binned, single wavelength groups will be shipped on any one bag. In order to ensure availability, single wavelength groups will not be orderable.

 $^{^{1)}}$ T_{amb} = 25 °C, unless otherwise specified

TLDR5800/TLDR6800

Vishay Semiconductors



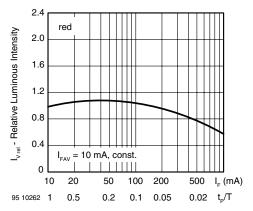


Figure 7. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

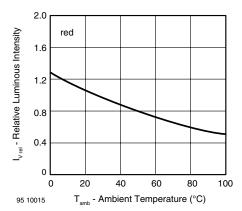
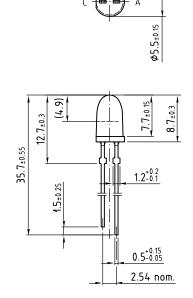
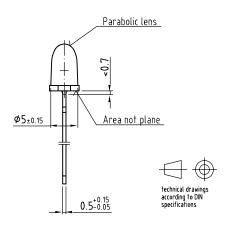


Figure 8. Rel. Luminous Intensity vs. Ambient Temperature

PACKAGE DIMENSIONS: TLDR5800



Drawing-No.: 6.544-5310.01-4 Issue: 2; 04.07.03 95 11476



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PACKAGE DIMENSIONS: TLDR6800

